

G(

isc N-Channel MOSFET Transistor

IXTH22N50P

D(2)

S(3)

pin 1.Gate

2.Drain 3. Source

• FEATURES

- With TO-3PN packaging
- · With low gate drive requirements
- Easy to drive
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

| • ABSO | LUTE MAXIMUM RATINGS(Ta=2 | 1 2 3 TO-247 package | | | | |
|------------------|------------------------------------|---|------|---|--|--|
| SYMBO L | PARAMETER | VALUE | UNIT | | | |
| V _{DSS} | Drain-Source Voltage | 500 | V | | | |
| V _{GSS} | Gate-Source Voltage | ±30 | V | | | |
| ID | Drain Current-Continuous | 22 | A | ĸ | | |
| I _{DM} | Drain Current-Single Pulsed | 66 | A | | | |
| P _D | Total Dissipation | 350 | W | MM DIM MIN MAX A 19.80 20.20 | | |
| Tj | Operating Junction Temperature | -55~150 | °C | B 15.40 15.80 C 4.90 5.10 D 0.90 1.10 | | |
| T _{stg} | Storage Temperature | -55~150 | °C | E1.401.60F1.902.10 | | |
| • THER | MAL CHARACTERISTICS | G 10.80 11.00 H 2.40 2.60 J 0.50 0.70 | | | | |
| SYMBOL | PARAMETER | MAX | UNIT | K19.5020.50P3.904.10 | | |
| Rth(ch-c) | Channel-to-case thermal resistance | 0.35 | °C/W | Q 3. 30 3. 50 U 5. 20 5. 40 V 2. 90 3. 10 | | |
| | • | | | 1 2.70 5.10 | | |

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ELECTRICAL CHARACTERISTICS

$T_{\texttt{C}}\text{=}25^{\circ}\!\!\mathbb{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|--|-----|-----|---------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 500 | | | v |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} =±30V; I _D =0.25mA | 3 | | 5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =11A | | | 270 | mΩ |
| lgss | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} =0V | | | ±0.01 | μ Α |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 500V; V _{GS} = 0V@Tc=25℃ Tc=125℃ | | | 5 50 | μA |
| VSDF | Diode forward voltage | I _{SD} =16A, V _{GS} = 0 V | | | 1.5 | V |

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